

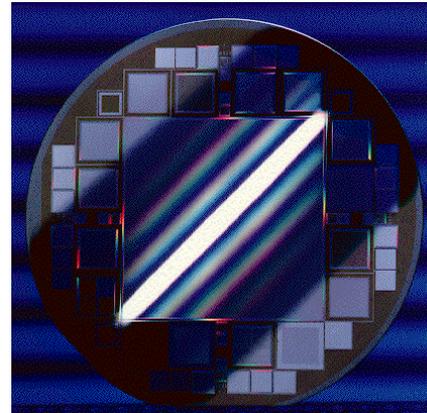
Overview of silicon strip detectors in current (ZEUS - ep) and future (CMS - pp) experiments

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BNL

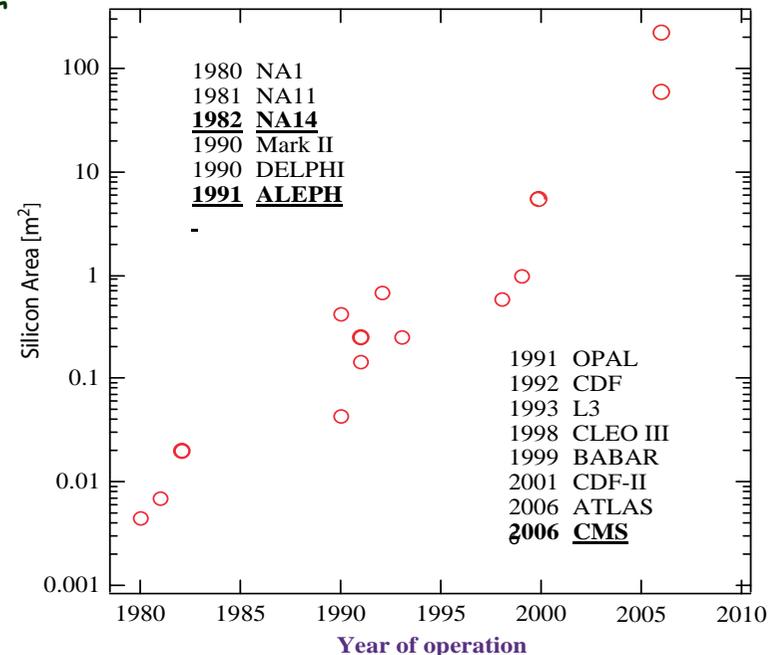
Introduction

■ General comment on silicon strip detectors

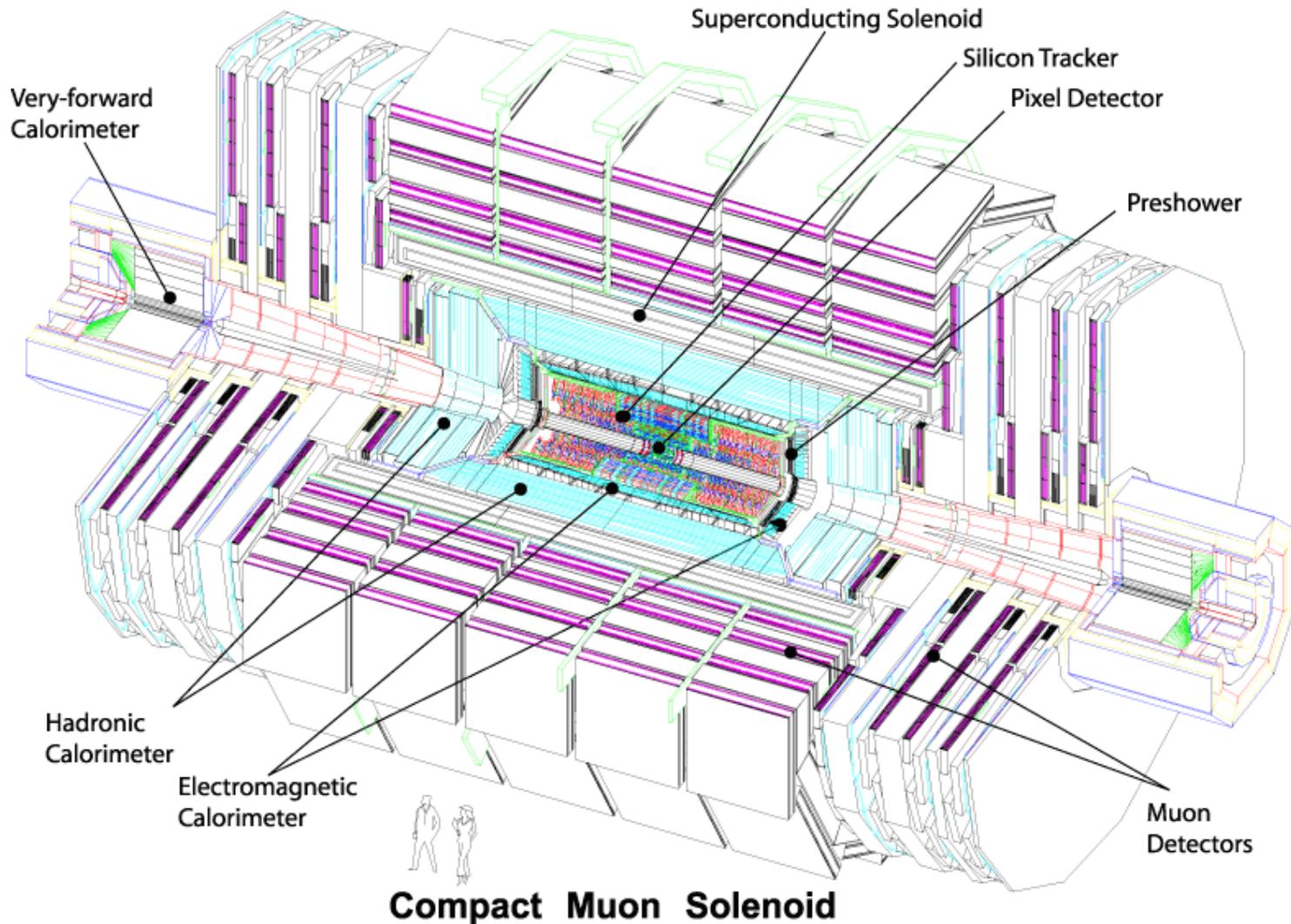
- Application of silicon strip detectors in particle and nuclear physics: ~25 years!
- By now, routinely used for:
 - ⇒ Precise tracking information
 - ⇒ Reconstruction of secondary vertices (Heavy flavor physics!)
- Fast readout (ns scale)
- Low material budget (Typical thickness: 300µm)



experiment	nb. of detectors	nb. of channels	silicon area [m ²]
CMS	15.95 k	10×10^6	223
ATLAS	16.0/2 k	6.15×10^6	60
AMS 2	2.3 k	196 k	6.5
DO 2		793 k	4.7
CDF SVX II	720	405 k	1.9
Babar		140 k	0.95
Aleph	144	95 k	0.49
L3	96	86 k	0.23



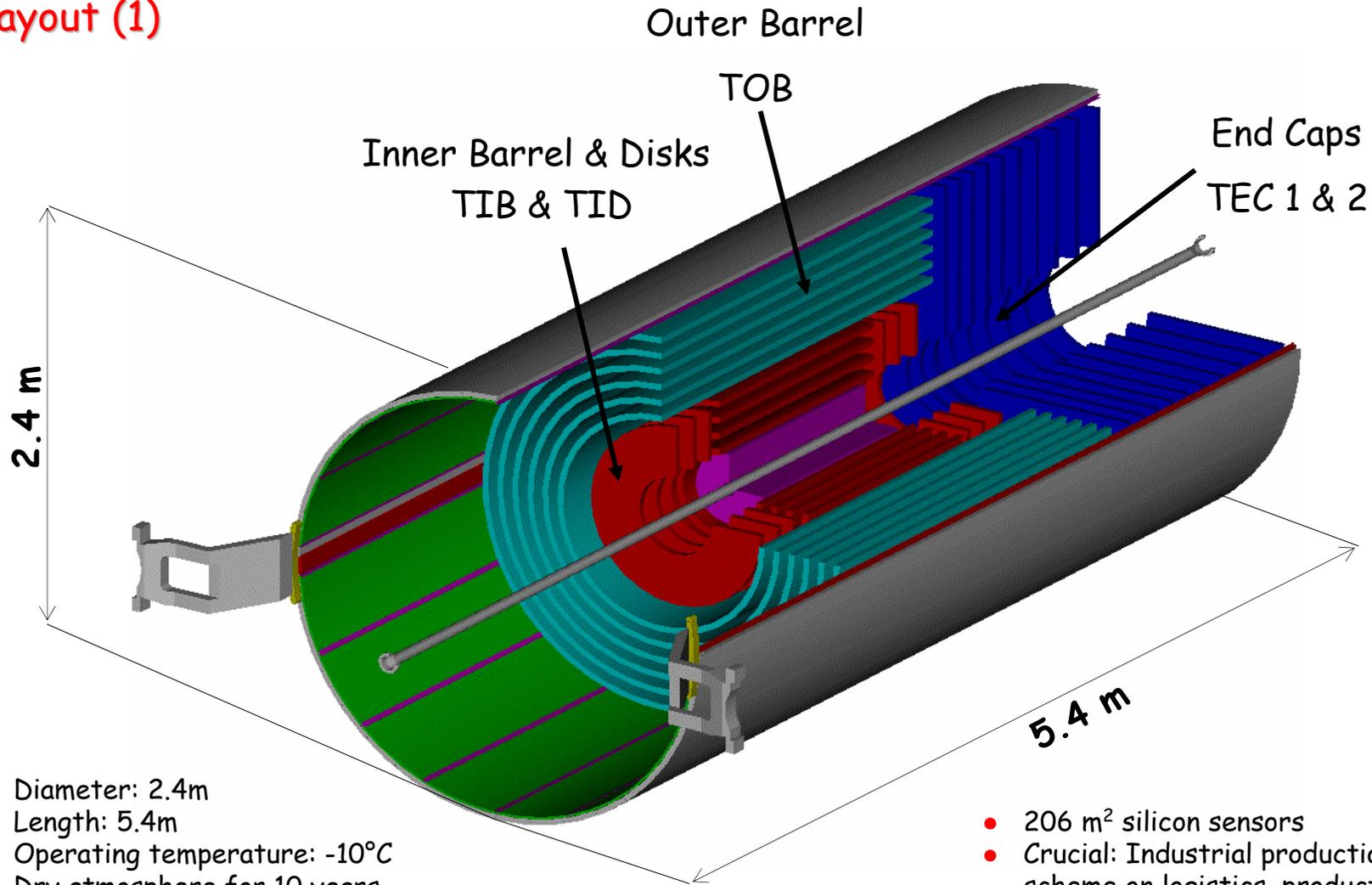
■ Overview



■ Requirements on tracking system

- Characterization of events involving heavy gauge bosons (W, Z) in particular through their leptonic decay
- Acceptance for $|\eta| < 2.5$
- Momentum resolution for isolated leptons in the central rapidity region:
$$\frac{\Delta p_T}{p_T} = 0.1 \times p_T$$
- Ability both to tag and to reconstruct in detail b-jets and B-hadrons within jets
- Reconstruction efficiency:
 - ⇒ > 95% for isolated high p_T tracks and
 - ⇒ > 90% for high p_T tracks with jets
- Resistance to high radiation dose
- Fast detector response (< 25ns) to reduce pile-up effects
- Minimal amount of material in front of the calorimeter
- Integration into the CMS trigger system

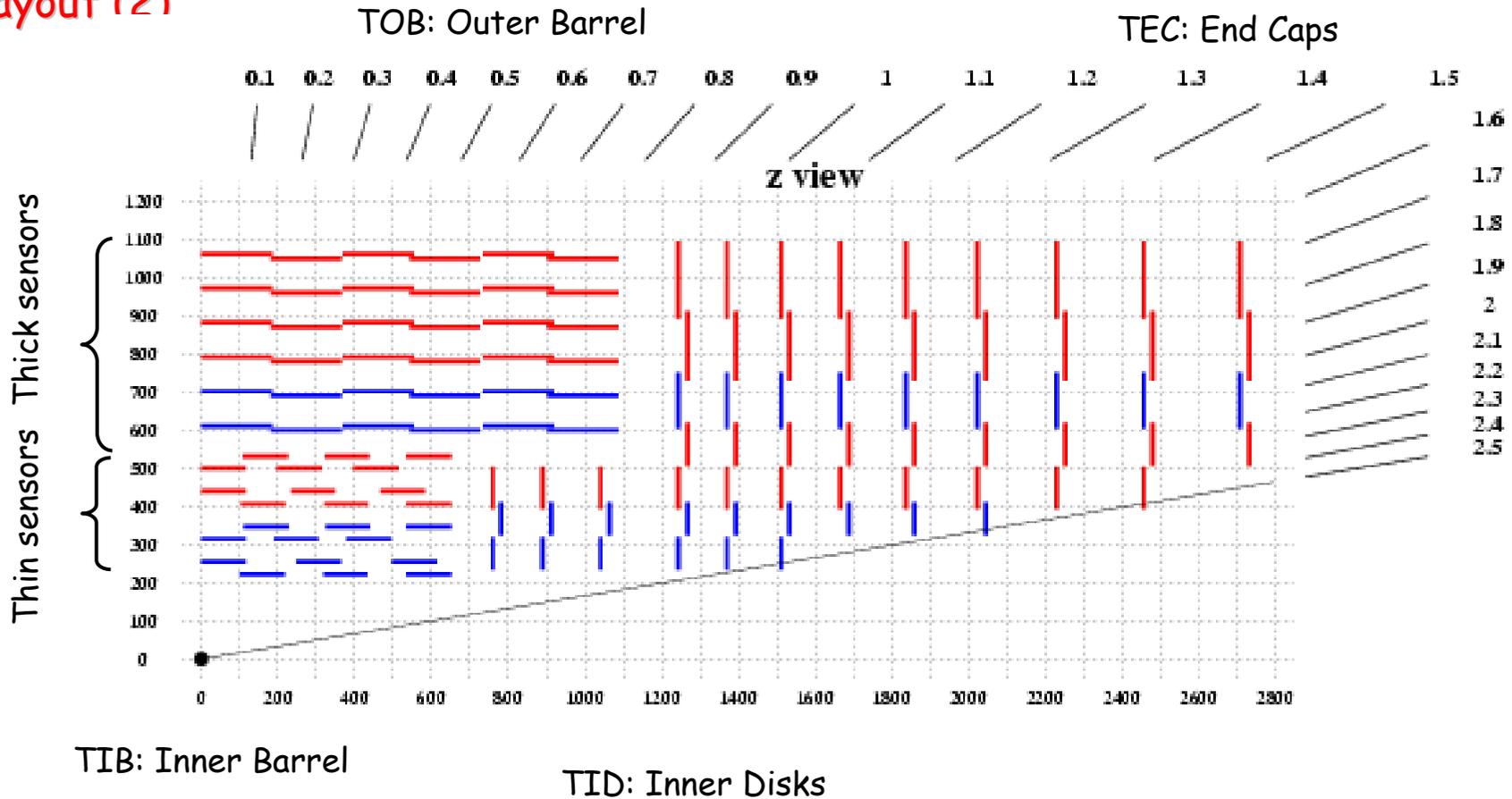
Layout (1)



- Diameter: 2.4m
- Length: 5.4m
- Operating temperature: -10°C
- Dry atmosphere for 10 years
- Expected rad. levels: $1.6 \cdot 10^{14}$ MeV eq. neutrons / cm²

- 206 m² silicon sensors
- Crucial: Industrial production scheme on logistics, production and quality assurance

Layout (2)

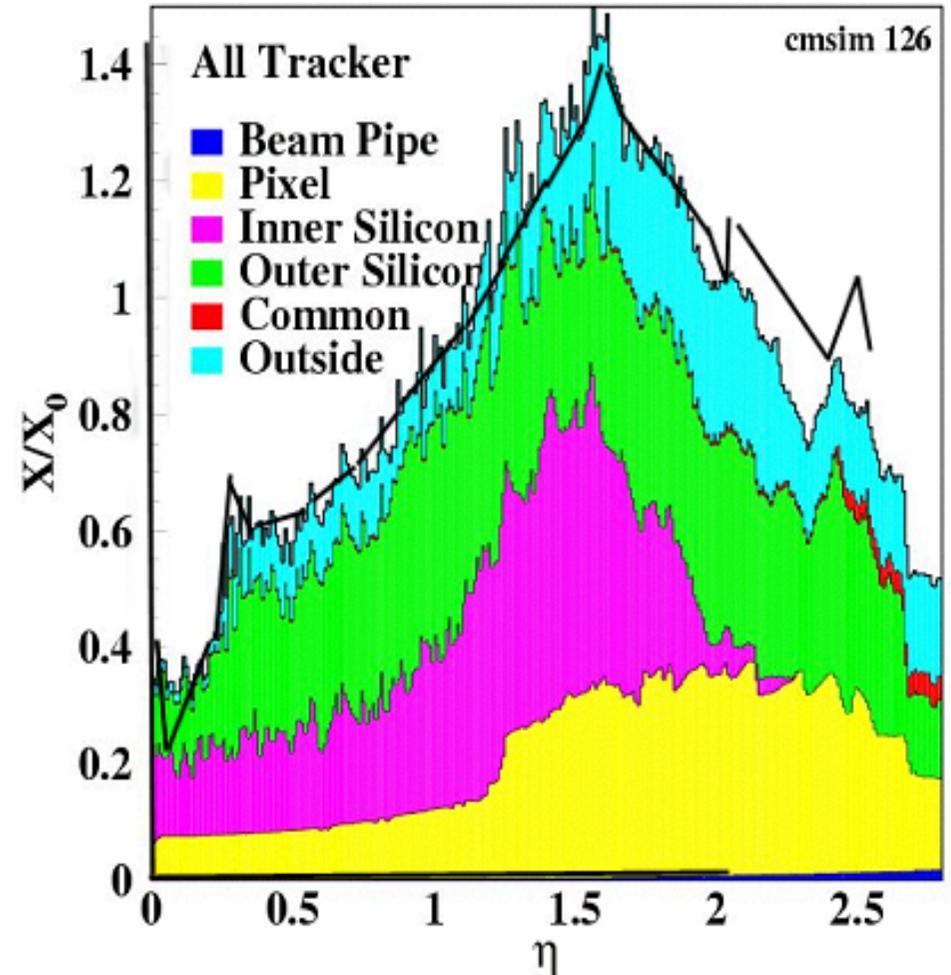
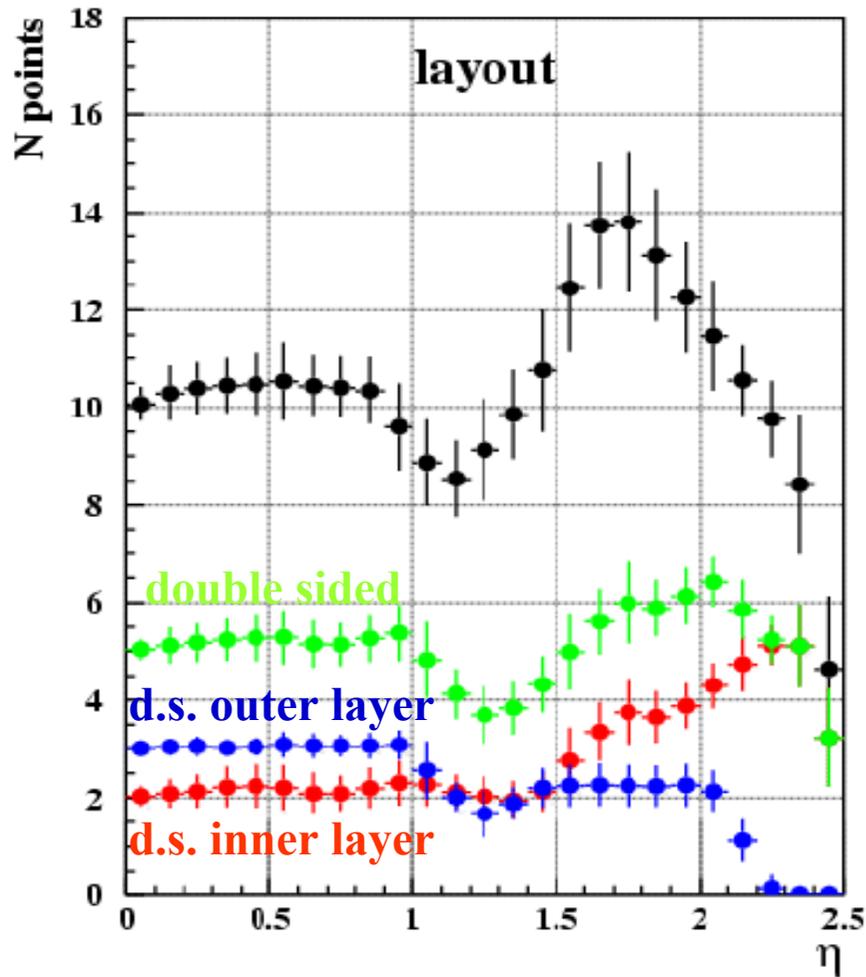


- Total modules: 8,608 **single-sided** modules and 3,312 **double-sided** detector modules
- ⇒ 15,232 single-sided equivalent modules!

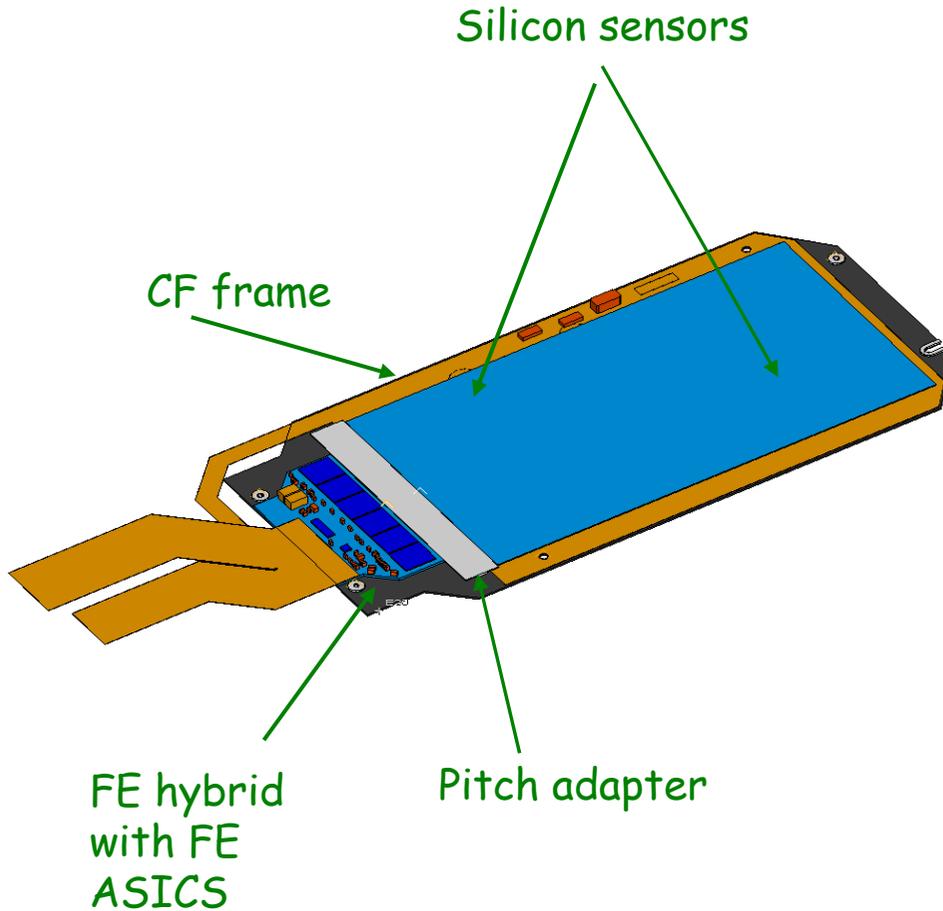
- Strip length / Thickness:

- ⇒ For $r \leq 55\text{cm}$: 11.9cm / 300 μm
- ⇒ For $r > 55\text{cm}$: 18.9cm / 500 μm

Layout (3) (Number of hit points and dead material budget)



■ Module components and accounting:



- 6,136 Thin sensors
- 18,192 Thick sensors

- 6,136 Thin detectors (1 sensor)
- 9,096 Thick detectors (2 sensors)

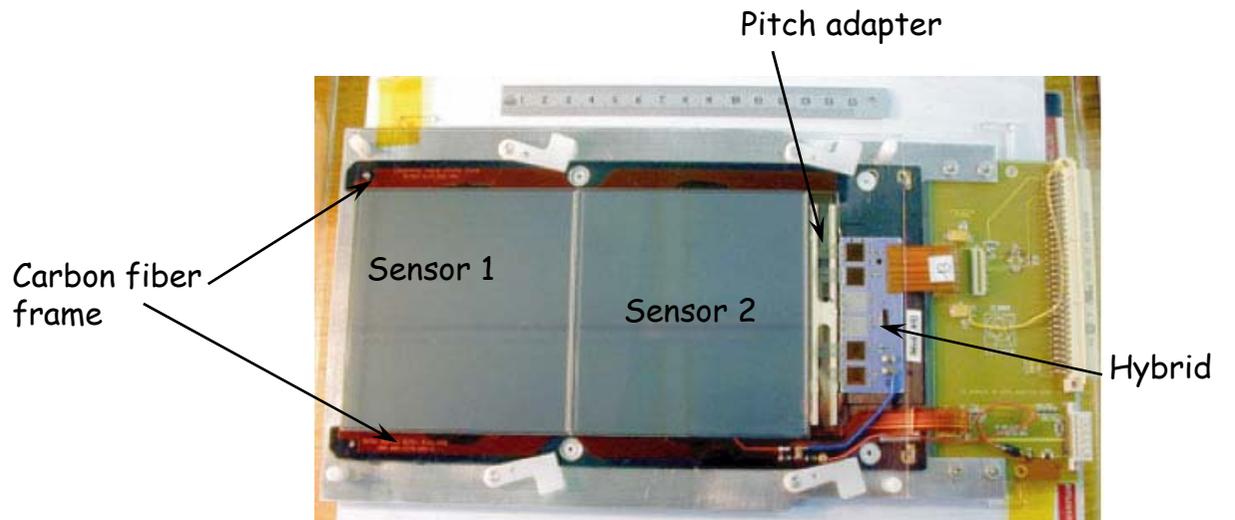
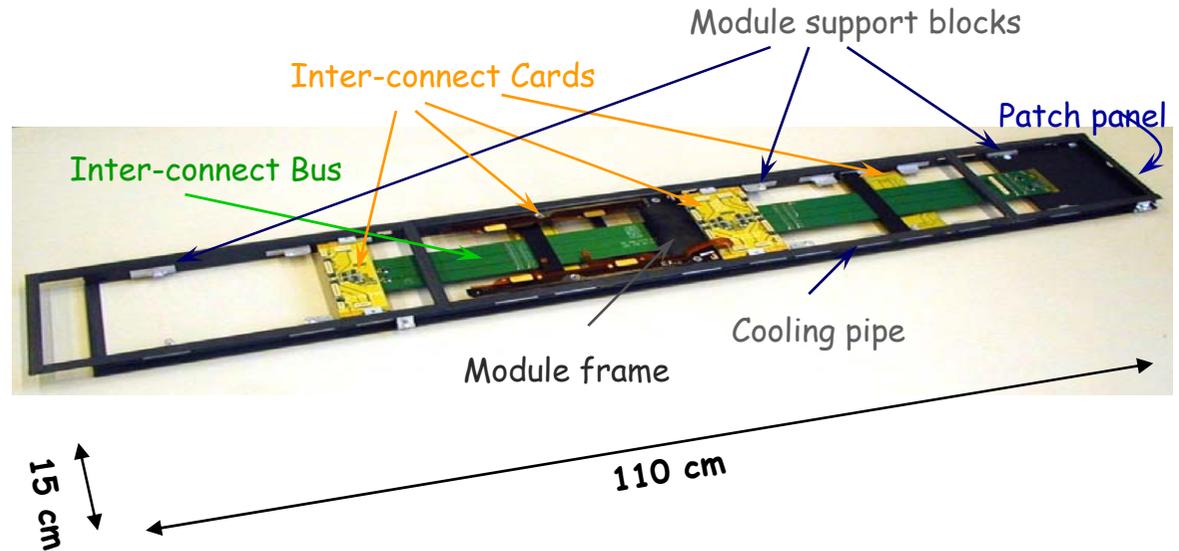
- 3112 + 1512 Thin modules (ss +ds)
- 5496 + 1800 Thick modules (ss +ds)

- 9,648,128 strips \equiv electronics channels

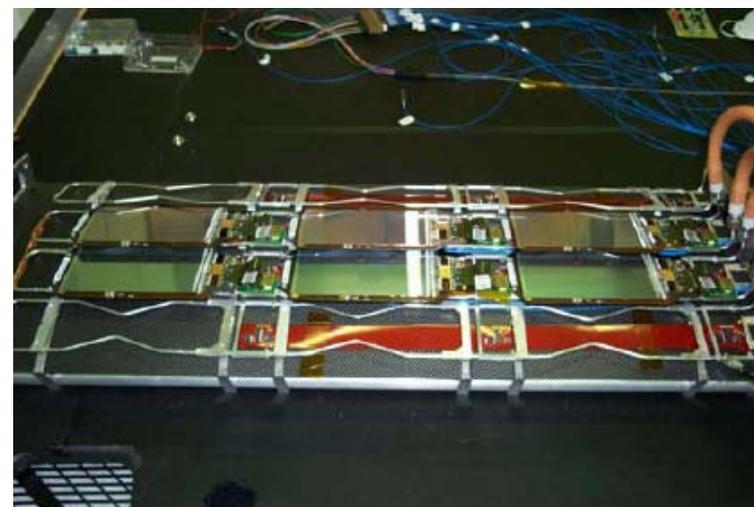
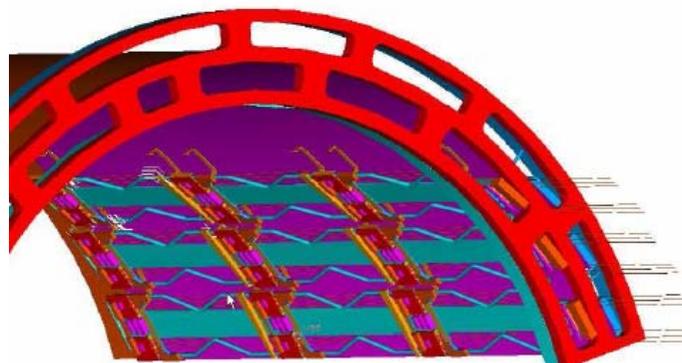
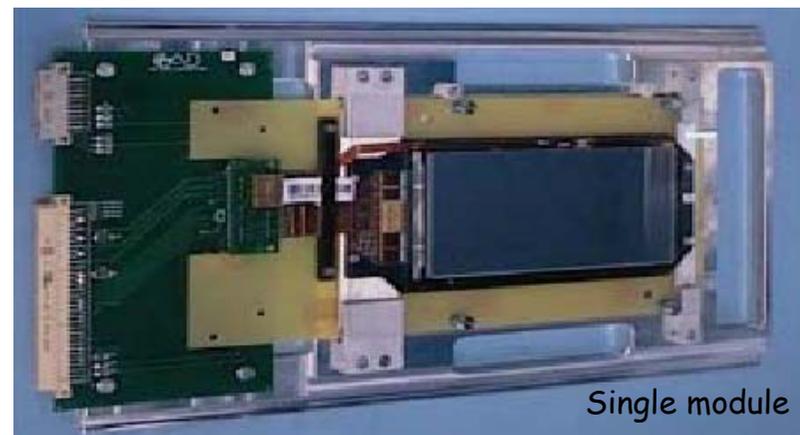
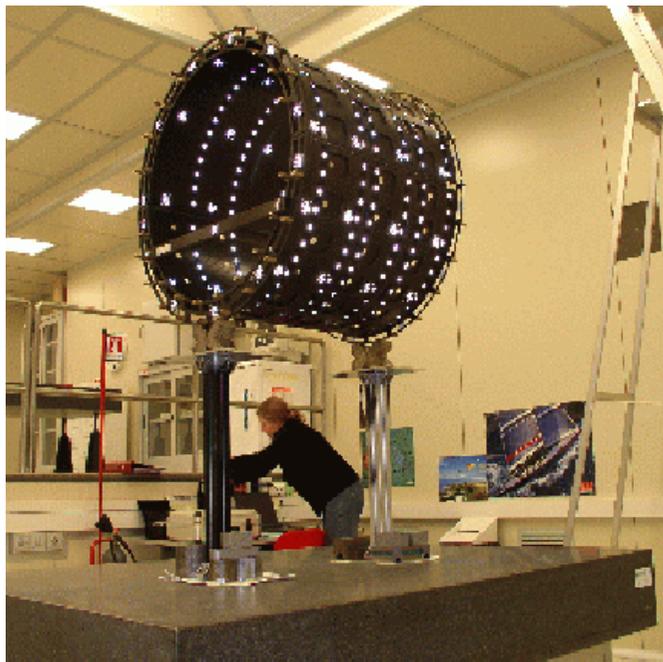
- 75,376 APV chips
-
- 25,000,000 Bonds

- 440 m² of silicon wafers
- 210 m² of silicon sensors (162m² + 48m²)

■ Tracker Outer Barrel: TOB

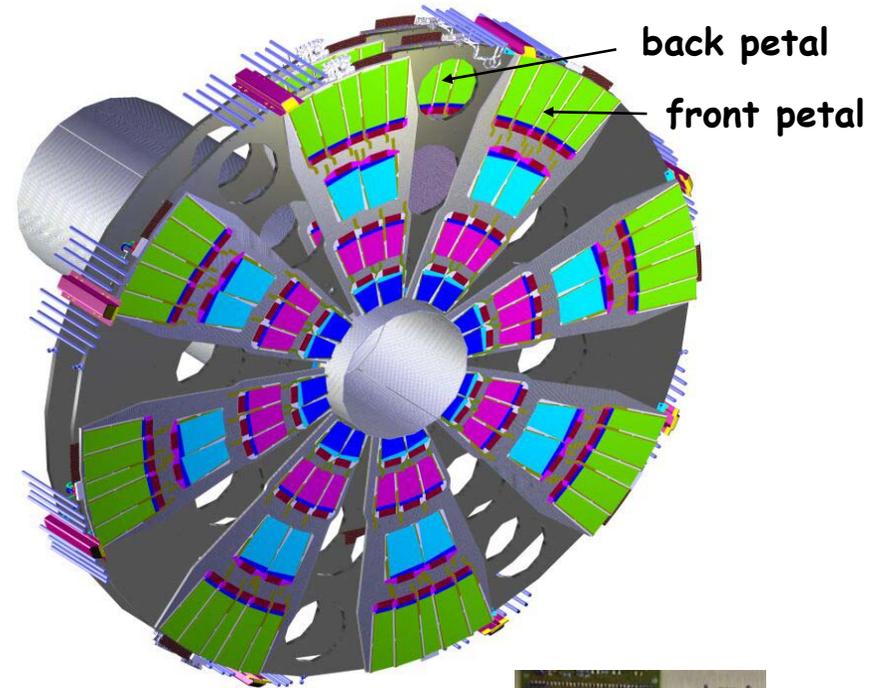


■ Tracker Inner Barrel and Disk: TIB and TID



Tracker End-Cap: TEC

- Two end-caps with 9 wheels each
- On each wheel: 8 front and 8 back petals
- Wedge shaped modules mounted on petals
- Petals can be extracted and inserted individually



■ Choice of silicon sensors and readout

● Sensors:

- Single-sided silicon strip detectors: p+ on n, AC coupled with polysilicon bias resistors of $1.5M\Omega$
- Different geometry (rectangular and wedge shaped) with varying strip pitch (80 - 200 μm) and strip length (9 - 20 cm) moving from smaller to larger radii
- Compensation for higher capacitance by longer strip sensors by thicker substrate: 300 μm for $r \leq 50\text{cm}$ and 500 μm for $r > 50\text{cm}$
- Resistivity: 1.3-3.0k Ωcm for thin and 3.5-70k Ωcm for thick sensors
- 14 different sensor designs
- Two manufactures: Hamamatsu (thin sensors) and STMicroelectronics (thick sensors)
- Quality: Better acceptance rate in case of Hamamatsu

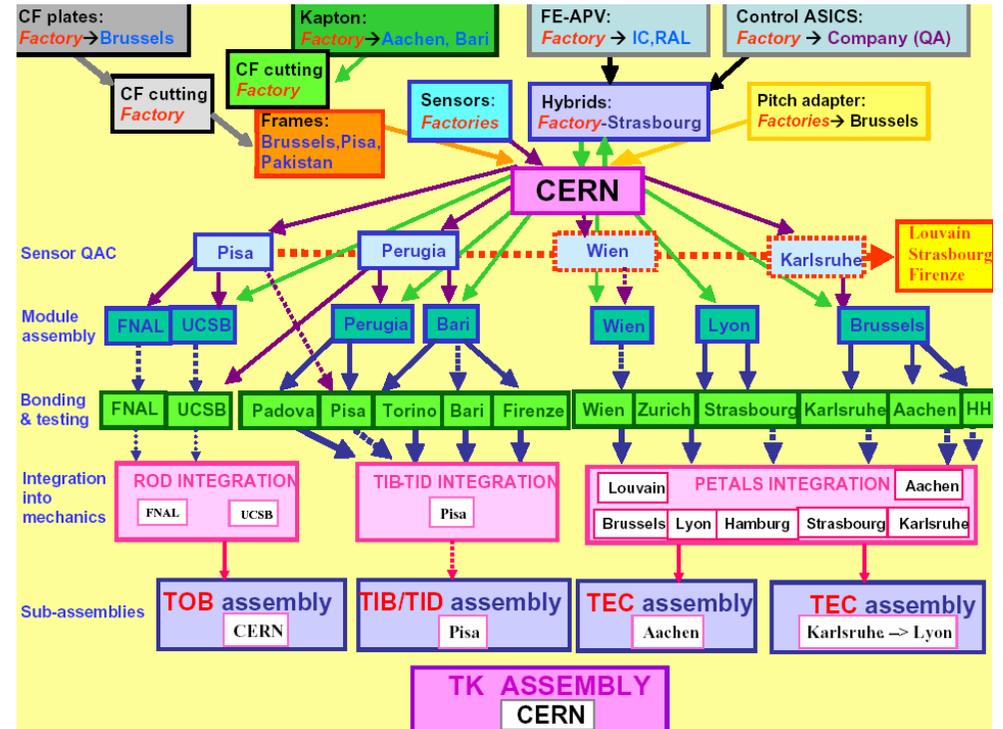
Extensive R&D programs have been carried out to investigate sensor type, geometry and substrate by means of simulations, irradiations, electrical characterization and beam tests!

● Readout: Analog readout based on APV chips

- Charge sensitive amplifier and shaper with 50ns shaping time
- Analog pipeline: 40MHz sample frequency and storing of samples in pipeline memory for a time equal to the L1 trigger latency (3.2 μs)

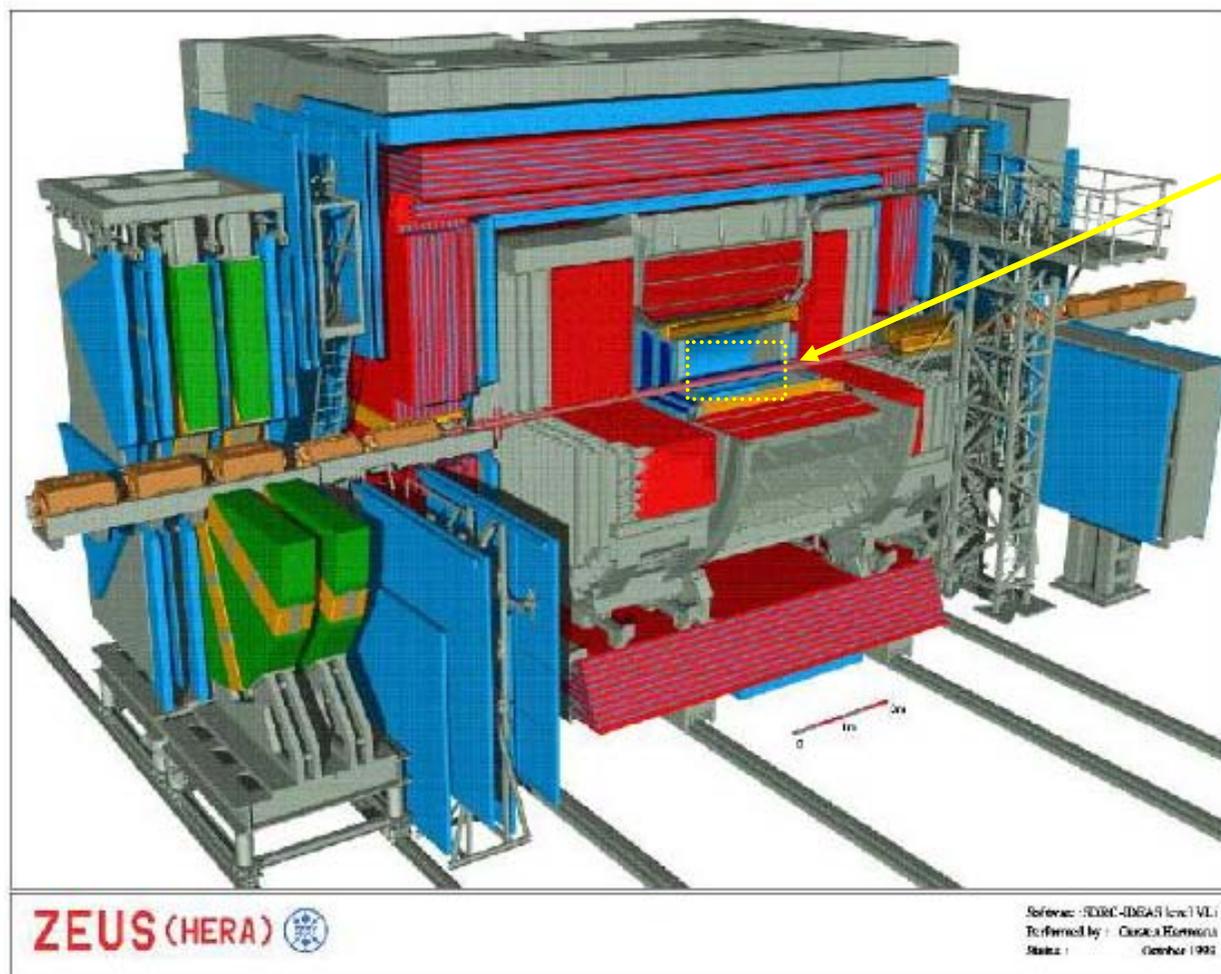
■ Production

- Quality assurance, assembly and bonding will be realized under quasi-industrial conditions with high multiplicity:
 - 4 centers are testing the overall sensor quality using fully automatic probe stations
 - 3 centers are monitoring the process quality
 - 2 centers are checking the radiation hardness.
- Assembly robots in 7 centers, plus industrial bonding machines in 12 places ensure high quality and reliability over the long construction period
- All parameters and logistics are monitored using a global database
- Assembly: 50 modules/day
- Micro-bonding: 16 modules/day
- CMS module production: 2.5years



ZEUS

- The ZEUS Micro-Vertex Detector (MVD)



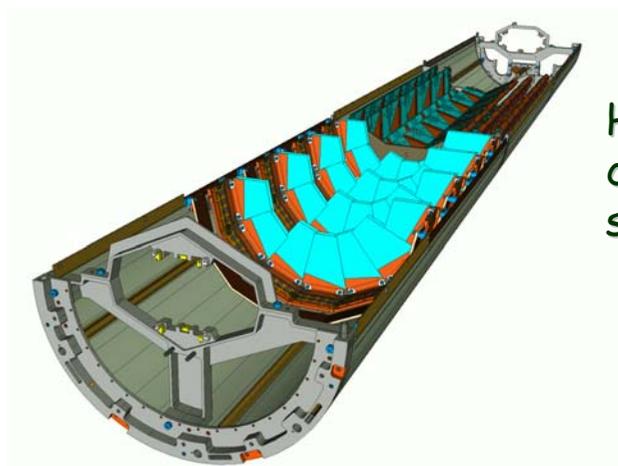
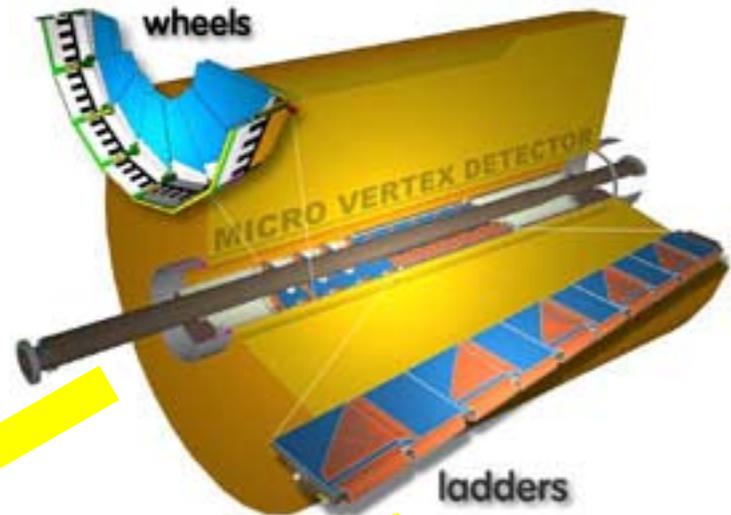
MVD

ZEUS

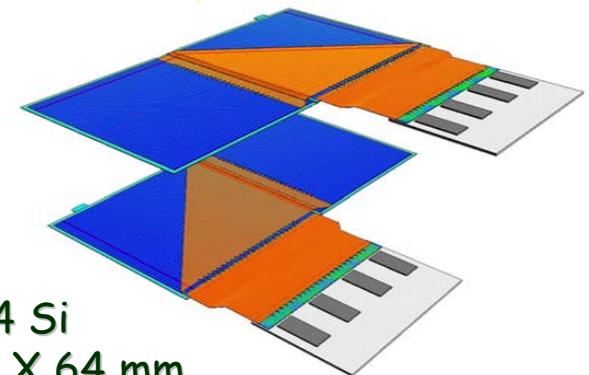
■ MVD design

The detector consists of a 65cm long **Barrel** with **3 layers** of Si detectors parallel to the beam. These layers are constructed of several carbon-fiber supports each with **5 Si module** (**Ladders**)

In the forward region there are **4 layers** of Si detectors, perpendicular to the beam. **14 modules** are mounted on a carbon-fiber support (**Wheel**)



Half MVD contained in a carbon-fiber sandwich support tube



Module with 4 Si detectors 64 X 64 mm

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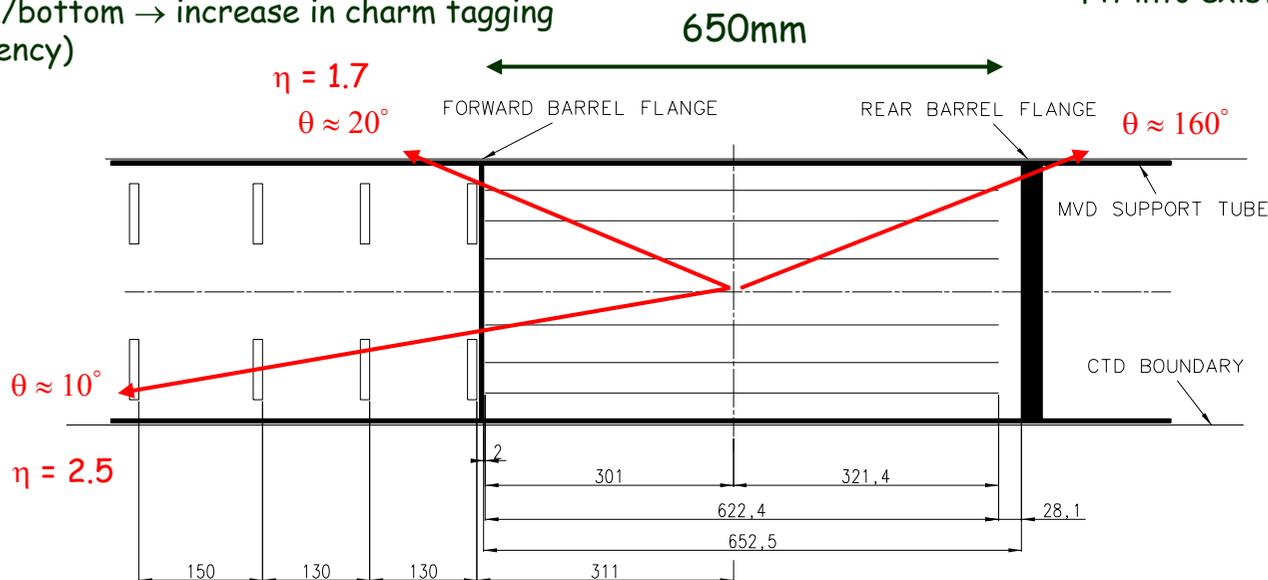
■ MVD design

● Motivation:

- Increase of angular acceptance in the forward direction (high Q^2 events)
- Improvement in the overall precision of the tracking system (momentum and impact parameter resolutions)
- Tagging events with displaced secondary vertices (long-lived particles e.g. weak decays of hadrons containing charm/bottom → increase in charm tagging efficiency)

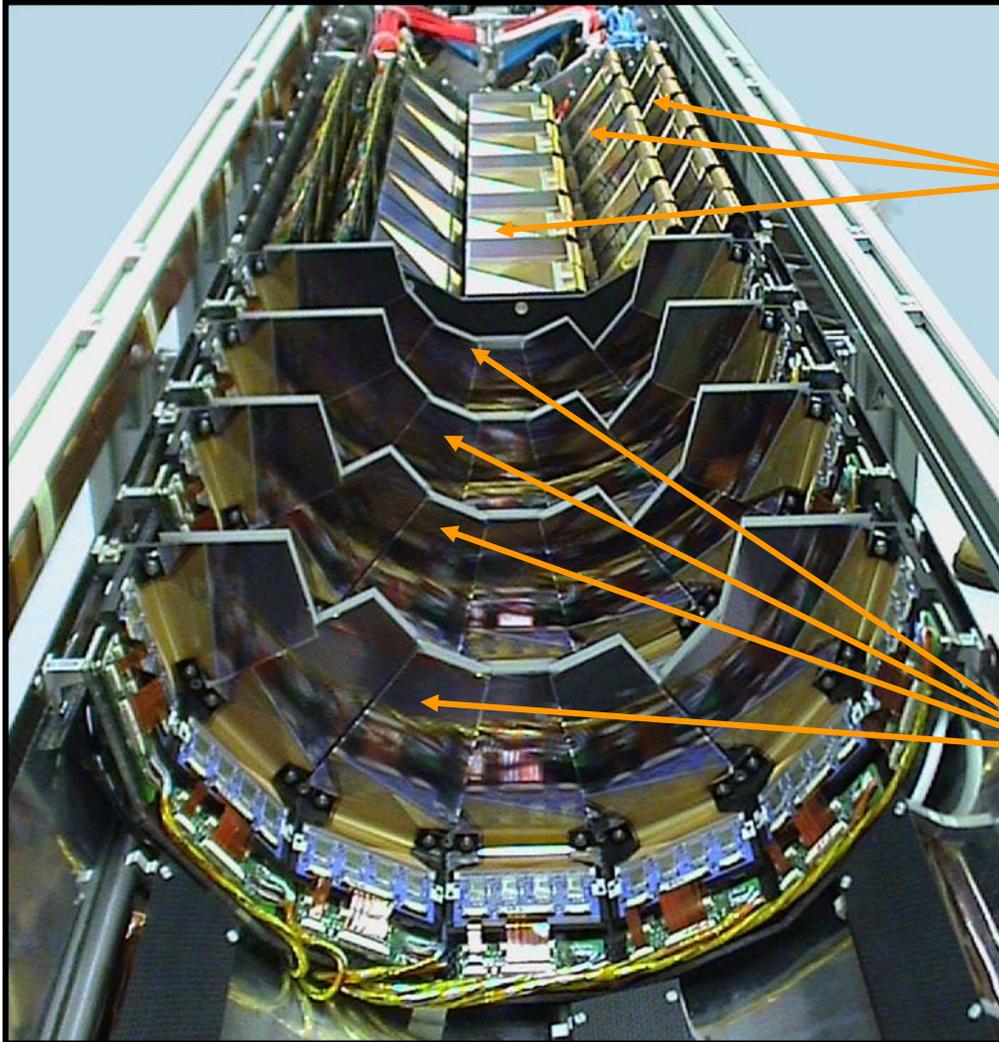
● Design considerations:

- Polar angle coverage: $10^\circ - 170^\circ$
- 3 spatial measurements in 2 projections per track
- Point resolution $\leq 20\mu\text{m}$
- Impact parameter resolution $\sim 50\mu\text{m}$
- Hit efficiency $> 97\%$
- Two-track separation $\sim 200\mu\text{m}$
- Alignment accuracy $\sim 20\mu\text{m}$
- Fit into existing detector layout



ZEUS

■ MVD design



● Barrel MVD:

- 3 cylinders: 4, 10 and 16 ladders
- 1 ladder: 5 modules
- 1 module: 1 (r-z, r- ϕ) + 1 (r- ϕ) half-module
- 1 half-module: 512 readout channels

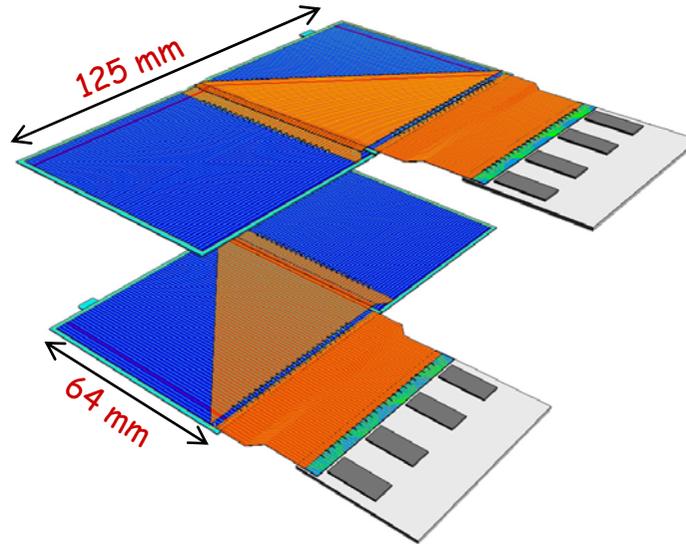
● Forward MVD:

- 4 wheels: 14 sectors
- 1 sector: 2 trapezoidal sensors (r- ϕ)
- 1 sensor: 480 readout channels

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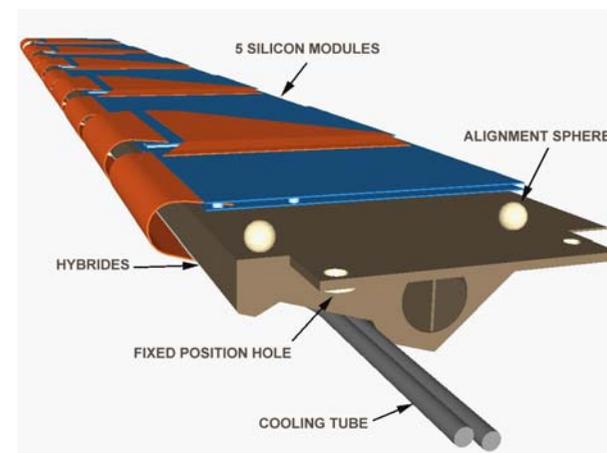
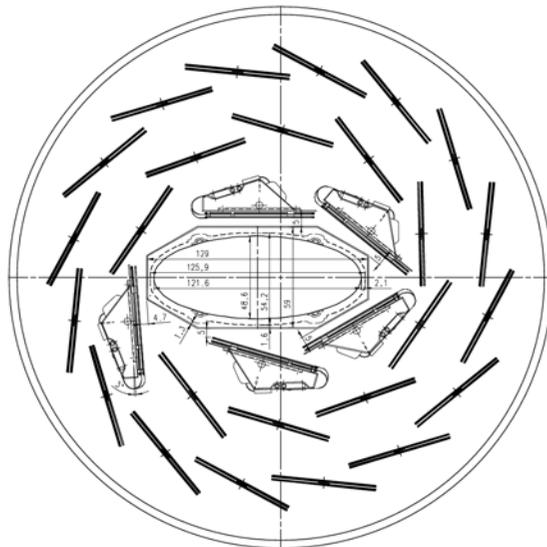
■ Barrel modules

- Two single side sensors are glued and bonded to gold strips plated on Upilex flex foils, and finally to a FE hybrid
- Two planes are glued together to form a module with x-y readout

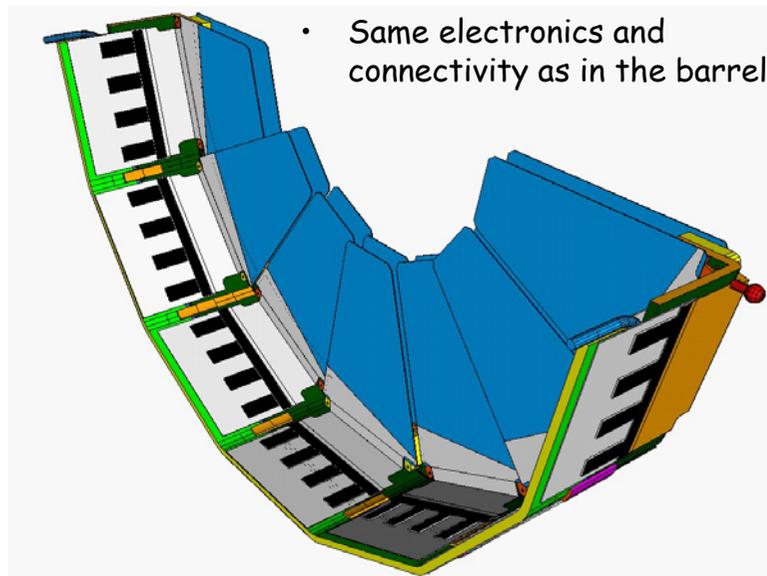
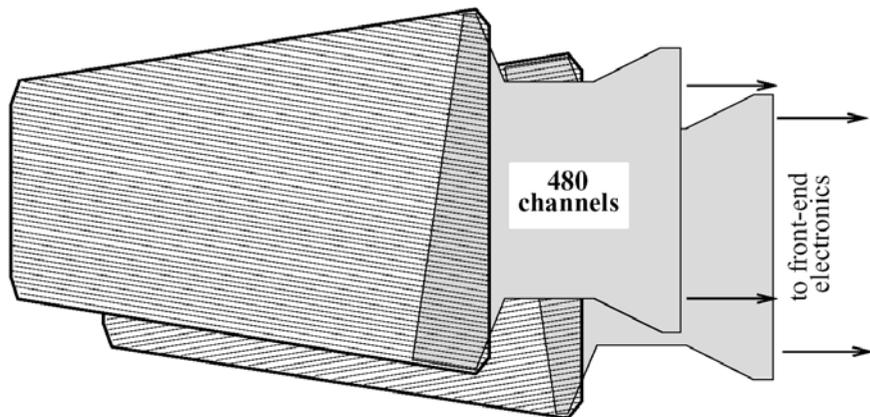


- Five modules are mounted on a carbon fiber support structure to form a ladder.
- The Si planes, Hybrids and Cabling are located on the 3 planes of the ladder

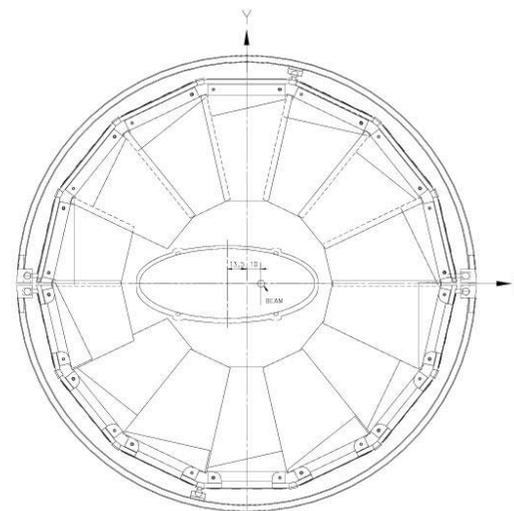
- 30 ladders, in 3 planes, are positioned around the elliptical beam pipe in the MVD barrel detector



■ Forward wheel modules



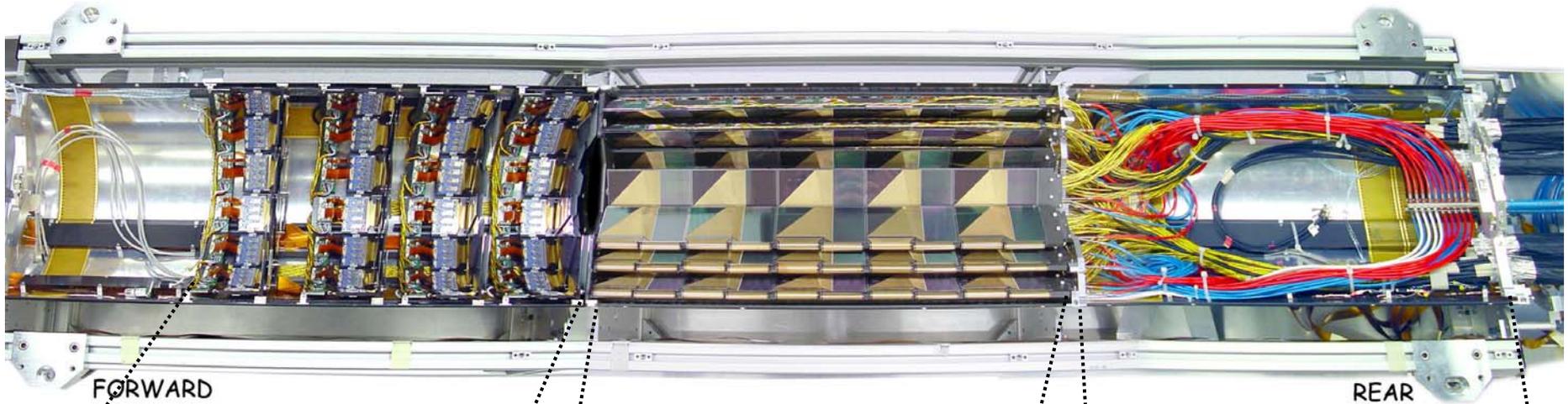
- The forward wheels have detector differently shaped (trapezoidal with two different sizes to accommodate the beam pipe)
- Two layers of single side Si detectors, same pitch and construction as in the barrel, strips cross at an angle of 26°



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■ Overall structure

One half of the entire MVD!



The forward section:

- 4 wheels
- each one composed by 2 layers of 14 Si detectors
- Total of 112 hybrids, >50k channels

The barrel section:

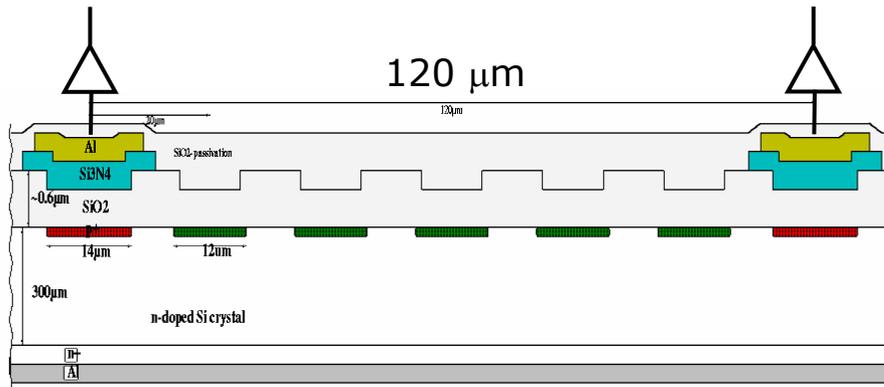
- 30 ladders
- each one composed of 5 modules of 4 Si detectors
- Total of 300 hybrids, >150k channels

The rear section:

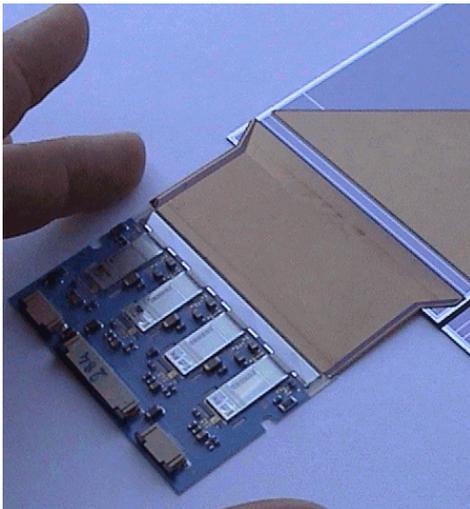
- Cooling pipes and manifolds
- Distribution of FE, slow control and alignment cables

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■ Sensors and readout



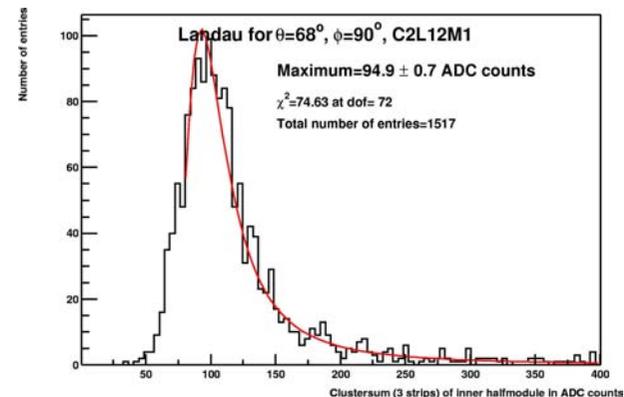
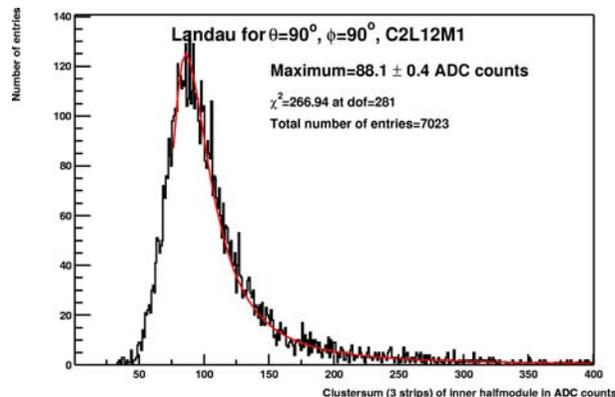
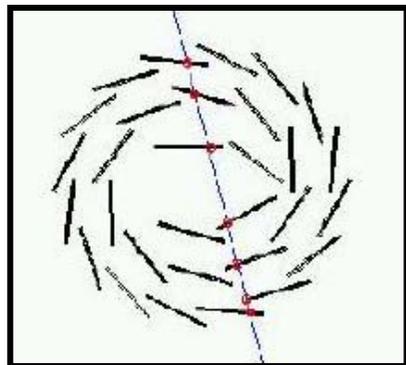
- n-doped silicon wafers (300 μm thickness) with p+ implantations (12 or 14 μm wide), HAMAMATSU
- 512 readout AC coupled channels in the barrel, 480 in the wheels
- Using the capacitive *charge sharing*, the analogue readout of one strip every 6 allows a good resolution ($<20 \mu\text{m}$) despite the readout pitch of 120 μm



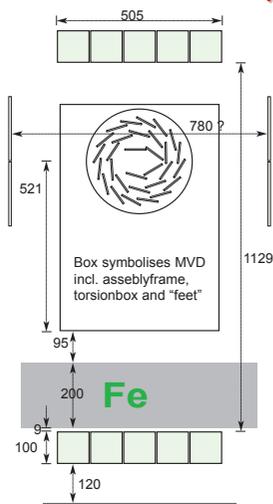
- Readout with analogue chip (HELIX3.0, Heidelberg+Nikhef) built with AMS 0.8 CMOS technology
- Only preamp, analog pipeline and drivers on chip
 - LVDS Clock and Control drivers 6m far on special patch boxes
 - ADCs 30m far on the MVD racks !
- Special care on cabling, signal handling, grounding, shielding!

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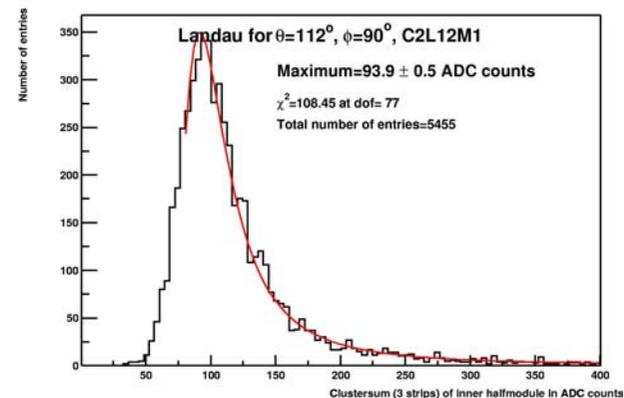
■ MVD performance (Cosmic ray test-stand)



Cosmic ray events during the MVD cosmic ray test



- Landau distributions selecting different angles for one detector module
- The peak positions scale with the respective impact angle



ZEUS

■ ZEUS MVD events display (High Q^2 DIS event)

